CMOS Delay-9 (H.0)
Interconnect Delay

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20170121

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References

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Some Figures from the following sites

[1] http://pages.hmc.edu/harris/cmosvlsi/4e/index.html Weste & Harris Book Site

[2] en.wikipedia.org





 Current in a wire is analogous to current in a pipe Resistance: narrow size impedes flow Capacitance: trough under the leaky pipe must fill first Inductance: paddle wheel inertia opposes changes in flow rate Negligible for most wires 	In	ntercon	nect N	Nodeli	ng
14: Wires CMOS VLSI Design ^{4th Ed.} 7	– Re – Ca – Ind	esistance: narrow apacitance: trough ductance: paddle Negligible for mo	size impedes n under the lea wheel inertia o	flow aky pipe must from the second se	es in flow rate
	14: Wires		CMOS VLSI Desigr	n 4th Ed.	7

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- Approxim	distributed system nate with lumped element model N segments rac arr arr arr arr arr arr arr arr arr	simulation
 14: Wires	CMOS VLSI Design 4th Ed.	8





 Comparable to gate capacitance Diffusion also has high resistance Avoid using diffusion <i>runners</i> for wires! Polysilicon has lower C but high R Use for transistor gates Occasionally for very short wires between gates 	 Diffusion also has high resistance Avoid using diffusion <i>runners</i> for wires! Polysilicon has lower C but high R Use for transistor gates Occasionally for very short wires between gates 	 Comparable to gate capacitance Diffusion also has high resistance Avoid using diffusion <i>runners</i> for wires! Polysilicon has lower C but high R Use for transistor gates Occasionally for very short wires between gates 	 Comparable to gate capacitance Diffusion also has high resistance Avoid using diffusion <i>runners</i> for wires! Polysilicon has lower C but high R Use for transistor gates Occasionally for very short wires between gates 	 Comparable to gate capacitance Diffusion also has high resistance Avoid using diffusion <i>runners</i> for wires! Polysilicon has lower C but high R Use for transistor gates Occasionally for very short wires between gates 	Diffusion & Polysilicon	
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					A: Wires CMOS VI SI Design 4th Ed.	19

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 * A Step tapered wire
* A tree with sized segments
* Varieties of wiring trees
* Steiner Tree
* Wire Sizing

